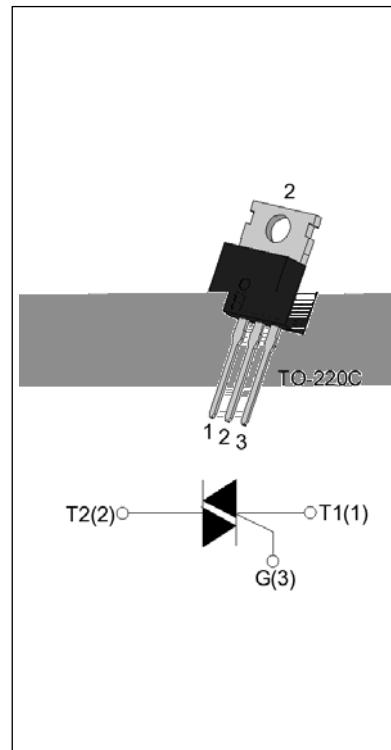




The JST06C-600CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST06C-600CW snubberless triac is especially recommended for use on inductive loads. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.



Symbol	Value	Unit
$I_{T(RMS)}$	6	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT} / /$	35/35/35	mA

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-125	
Repetitive peak off-state voltage ( $T_j=25^\circ C$ )	$V_{DRM}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ C$ )	$V_{RRM}$	600	V
RMS on-state current ( $T_c = 111^\circ C$ )	$I_{T(RMS)}$	6	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$ , $T_j=25^\circ C$ )	$I_{TSM}$	65	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$ , $T_j=25^\circ C$ )		72	
$I^2t$ value for fusing ( $t_p=10ms$ , $T_j=25^\circ C$ )	$I^2t$	21	$A^2s$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100Hz$ , $T_j=125^\circ C$ )	$dI/dt$	100	$A/\mu s$
Peak gate current ( $t_p=20\mu s$ , $T_j=125^\circ C$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125^\circ C$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W

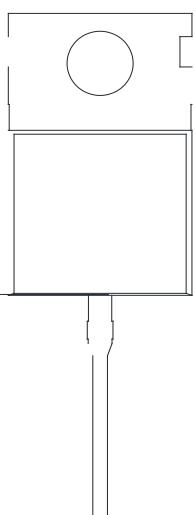
Peak pulse voltage (T <sub>j</sub> =25 ; non-repetitive,off-state;FIG.7)	V <sub>PP</sub>	3	kV
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(T<sub>j</sub>=25 unless otherwise specified)

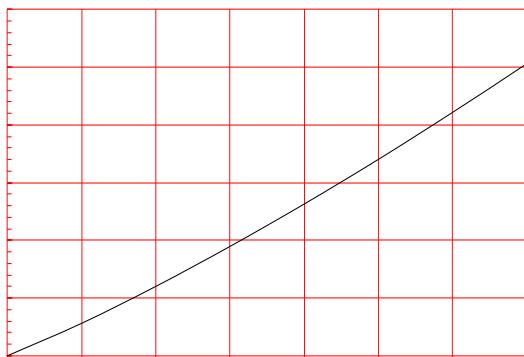
Symbol	Test Condition	Quadrant	Value		Unit
I <sub>GT</sub>	V <sub>D</sub> =12V R <sub>L</sub> =33	- -	MAX.	35	mA
V <sub>GT</sub>		- -	MAX.	1	V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> T <sub>j</sub> =125 R <sub>L</sub> =3.3K	- -	MIN.	0.2	V
I <sub>L</sub>	I <sub>G</sub> =1.2I <sub>GT</sub>	-	MAX.	50	mA
				60	
I <sub>H</sub>	I <sub>T</sub> =100mA		MAX.	35	mA
dV/dt	V <sub>D</sub> =400V Gate Open T <sub>j</sub> =125		MIN.	1500	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T <sub>j</sub> =125		MIN.	4	A/ms
t <sub>on</sub>	I <sub>G</sub> =40mA I <sub>A</sub> =200mA I <sub>R</sub> =20mA T <sub>j</sub> =25	TYP.	3	μs	
t <sub>off</sub>			30		

Symbol	Parameter	Value(MAX.)	Unit
V <sub>TM</sub>	I <sub>TM</sub> =8.5A t <sub>p</sub> =380μs	1.5	V
V <sub>TO</sub>	Threshold voltage	0.82	V
R <sub>D</sub>	Dynamic resistance	57	m
I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub>	5	μA
I <sub>RRM</sub>			

J	ST	06	C	-600	CW
JieJie Microelectronics Co., Ltd.					
	Triacs				
		IT(RMS):6A			
			C:TO-220C		
				CW:IGT1-3 35mA	
				600:VDRM /VRRM 600V	



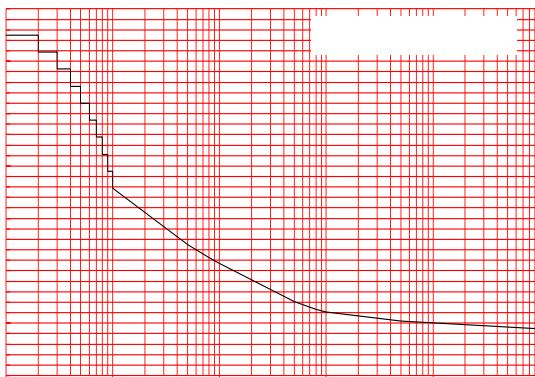
**FIG.1** Maximum power dissipation versus RMS on-state current



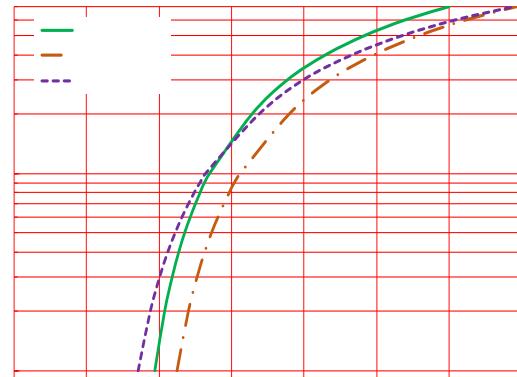
**FIG.2:** RMS on-state current versus case temperature



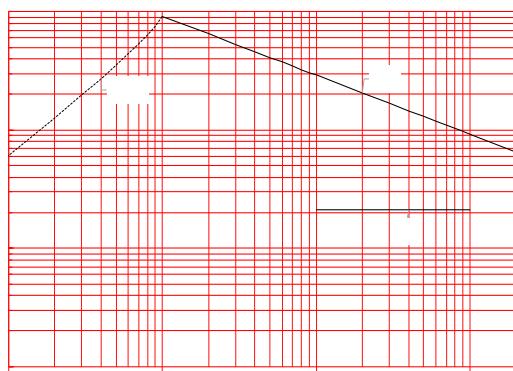
**FIG.3:** Surge peak on-state current versus number of cycles



**FIG.4:** On-state characteristics



**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 100\text{A}/\mu\text{s}$ )



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

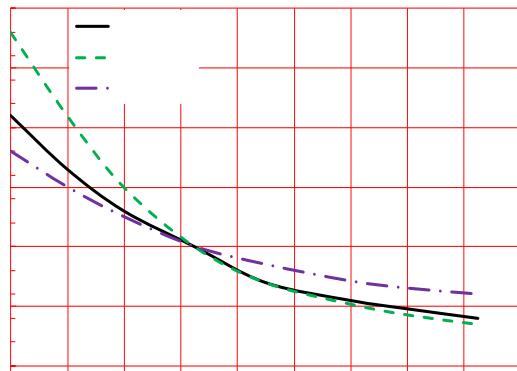
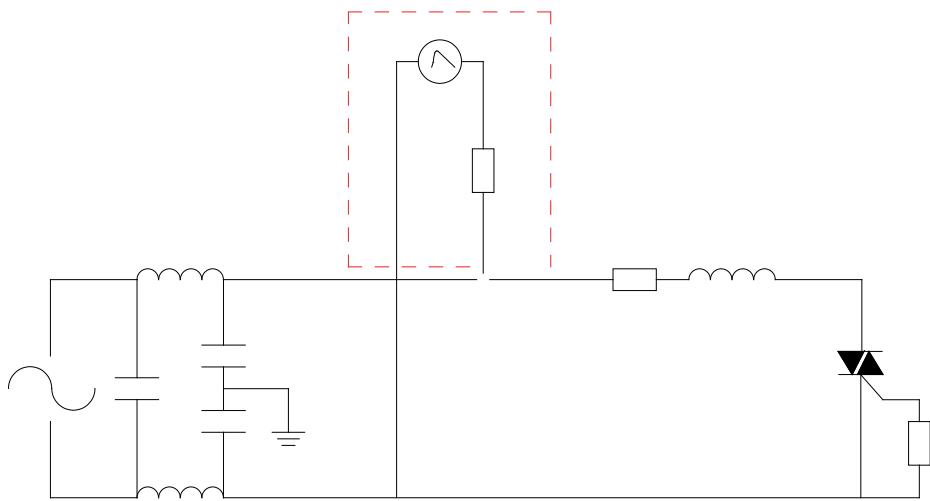


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
<b>JST06C-600CW</b>	<b>600</b>	<b>35</b>	<b>TO-220C</b>	<b>50</b>	<b>Tube</b>

#### Document Revision History

Date	Revision	Changes
Apr.11, 2023	A.1.0	Last updated



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